

MITSUBISHI IGBT MODULES

CM200RL-12NF

HIGH POWER SWITCHING USE

CM200RL-12NF



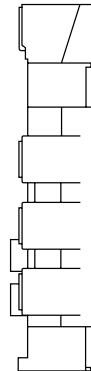
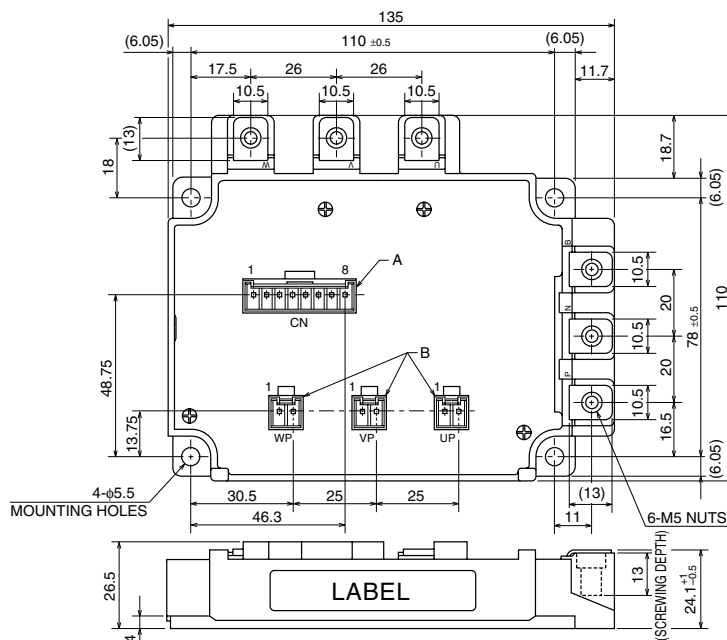
- Ic200A
- VCES600V
- Insulated Type
- 7-elements in a pack

APPLICATION

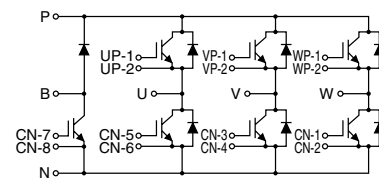
AC drive inverters & Servo controls, etc

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



Housing Type of A and B
(J.S.T.Mfg.Co.Ltd)
A = B8P-VH-FB-B, B = B2P-VH-FB-B



CIRCUIT DIAGRAM

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ABSOLUTE MAXIMUM RATINGS (Tj = 25°C, unless otherwise specified)

INVERTER PART

Symbol	Parameter	Conditions	Ratings	Unit
V _{CES}	Collector-emitter voltage	G-E Short	600	V
V _{GES}	Gate-emitter voltage	C-E Short	±20	V
I _C	Collector current	DC, T _C = 88°C ^{*1}	200	A
I _{CM}		Pulse (Note 2)	400	A
I _E (Note 1)	Emitter current		200	A
I _{EM} (Note 1)		Pulse (Note 2)	400	A
P _C (Note 3)	Maximum collector dissipation	T _C = 25°C	890	W

BRAKE PART

Symbol	Parameter	Conditions	Ratings	Unit
V _{CES}	Collector-emitter voltage	G-E Short	600	V
V _{GES}	Gate-emitter voltage	C-E Short	±20	V
I _C	Collector current	DC, T _C = 99°C ^{*1}	100	A
I _{CM}		Pulse (Note 2)	200	A
P _C (Note 3)	Maximum collector dissipation	T _C = 25°C	540	W
V _{RRM}	Repetitive peak reverse voltage	Clamp diode part	600	V
I _{FM}	Forward current	Clamp diode part	100	A

(COMMON RATING)

Symbol	Parameter	Conditions	Ratings	Unit
T _j	Junction temperature		−40 ~ +150	°C
T _{stg}	Storage temperature		−40 ~ +125	°C
V _{iso}	Isolation voltage	Terminals to base plate, f = 60Hz, AC 1 minute	2500	V _{rms}
—	Torque strength	Main terminals M5 screw	2.5 ~ 3.5	N • m
—		Mounting M5 screw	2.5 ~ 3.5	N • m
—	Weight	Typical value	750	g

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ELECTRICAL CHARACTERISTICS (T_j = 25°C, unless otherwise specified)

INVERTER PART

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
ICES	Collector cutoff current	VCE = VCES, VGE = 0V	—	—	1	mA
VGE(th)	Gate-emitter threshold voltage	IC = 20mA, VCE = 10V	6	7	8	V
IGES	Gate leakage current	±VGE = VGES, VCE = 0V	—	—	0.5	μA
VCE(sat)	Collector-emitter saturation voltage	IC = 200A, VGE = 15V	—	1.7	2.2	V
		T _j = 25°C	—	1.7	—	
		T _j = 125°C	—	—	—	
Cies	Input capacitance	VCE = 10V	—	—	30	nF
Coes	Output capacitance	VGE = 0V	—	—	3.7	nF
Cres	Reverse transfer capacitance		—	—	1.2	nF
QG	Total gate charge	VCC = 300V, IC = 200A, VGE = 15V	—	800	—	nC
td(on)	Turn-on delay time		—	—	120	ns
tr	Turn-on rise time	VCC = 300V, IC = 200A	—	—	100	ns
td(off)	Turn-off delay time	VGE = ±15V	—	—	300	ns
tf	Turn-off fall time	RG = 3.1Ω, Inductive load	—	—	300	ns
trr (Note 1)	Reverse recovery time	IE = 200A	—	—	150	ns
Qrr (Note 1)	Reverse recovery charge		—	4.8	—	μC
VEC(Note 1)	Emitter-collector voltage	IE = 200A, VGE = 0V	—	—	2.8	V
Rth(j-c)Q	Thermal resistance	IGBT part (1/6 module)*1	—	—	0.14	K/W
Rth(j-c)R		FWDi part (1/6 module)*1	—	—	0.22	K/W
Rth(c-f)	Contact thermal resistance	Case to heat sink, Thermal compound Applied (1/6 module)*2	—	0.051	—	K/W
RG	External gate resistance		3.1	—	31	Ω

BRAKE PART

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
ICES	Collector cutoff current	VCE = VCES, VGE = 0V	—	—	1	mA
VGE(th)	Gate-emitter threshold voltage	IC = 10mA	6	7	8	V
IGES	Gate leakage current	±VGE = VGES, VCE = 0V	—	—	0.5	μA
VCE(sat)	Collector-emitter saturation voltage	IC = 100A, VGE = 15V	—	1.7	2.2	V
		T _j = 25°C	—	1.7	—	
		T _j = 125°C	—	—	—	
Cies	Input capacitance	VCE = 10V	—	—	15	nF
Coes	Output capacitance	VGE = 0V	—	—	1.9	nF
Cres	Reverse transfer capacitance		—	—	0.6	nF
QG	Total gate charge	VCC = 300V, IC = 100A, VGE = 15V	—	400	—	nC
VFM	Forward voltage drop	IF = 100A	—	—	2.8	V
Rth(j-c)Q	Thermal resistance	IGBT part*1	—	—	0.23	K/W
Rth(j-c)R		Clamp diode part*1	—	—	0.41	K/W
RG	External gate resistance		6.3	—	63	Ω

*1 : Case temperature (T_c) measured point is just under the chips.

If you use this value, Rth(j-a) should be measured just under the chips.

*2 : Typical value is measured by using thermally conductive grease of λ = 0.9[W/(m • K)].

Note 1. IE, VEC, trr & Qrr represent characteristics of the anti-parallel, emitter-collector free-wheel diode (FWDi).

2. Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed T_{jmax} rating.

3. Junction temperature (T_j) should not increase beyond 150°C.

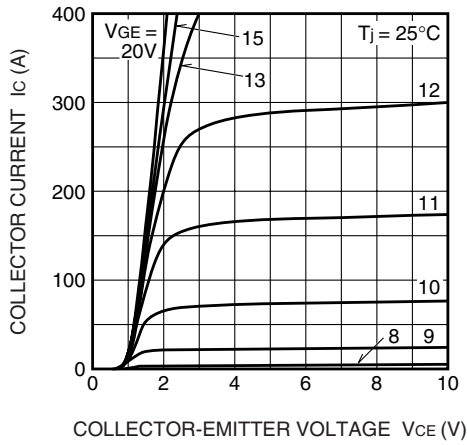
4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

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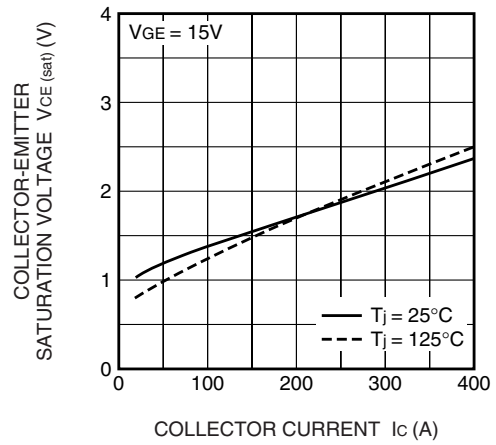
HIGH POWER SWITCHING USE

PERFORMANCE CURVES

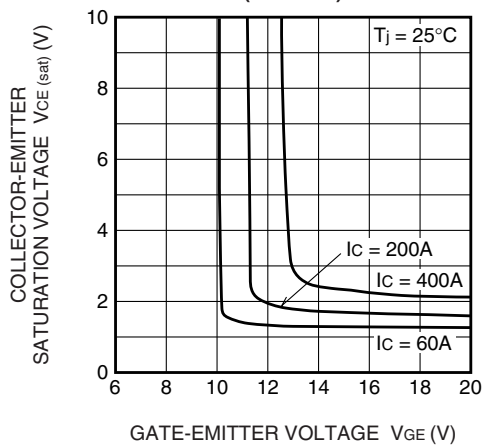
OUTPUT CHARACTERISTICS
(TYPICAL)



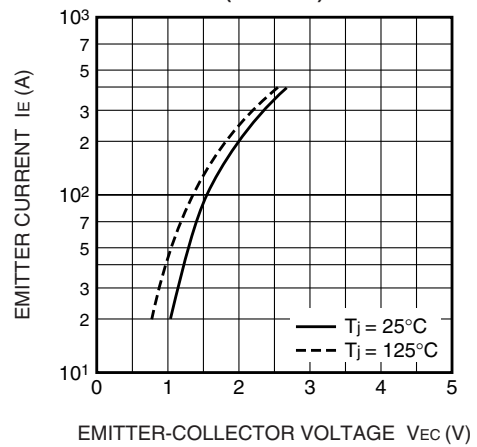
COLLECTOR-EMITTER SATURATION
VOLTAGE CHARACTERISTICS
(TYPICAL)



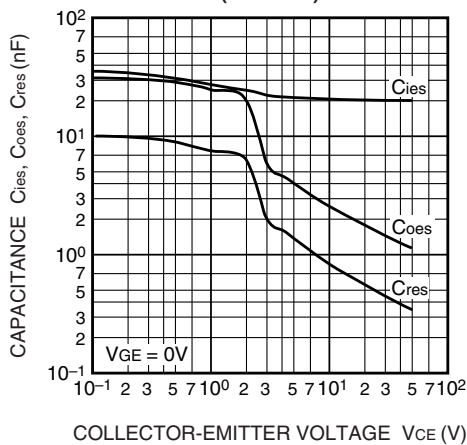
COLLECTOR-EMITTER SATURATION
VOLTAGE CHARACTERISTICS
(TYPICAL)



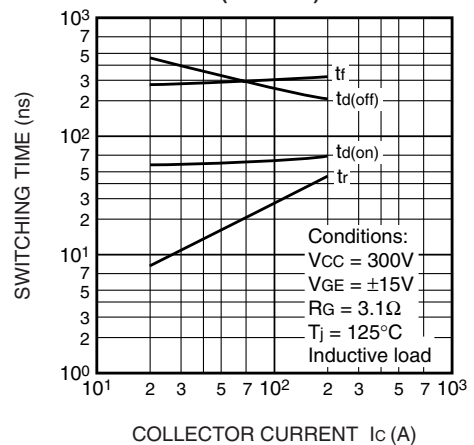
FREE-WHEEL DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



CAPACITANCE- V_{ce}
CHARACTERISTICS
(TYPICAL)



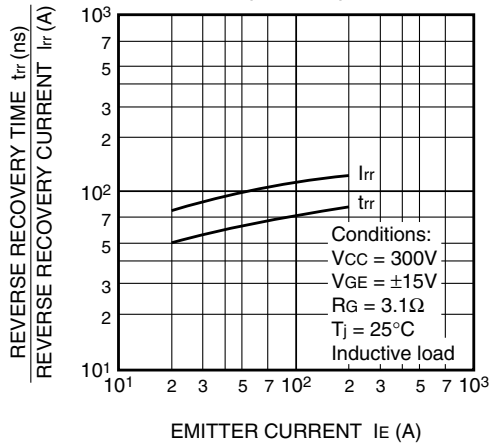
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)



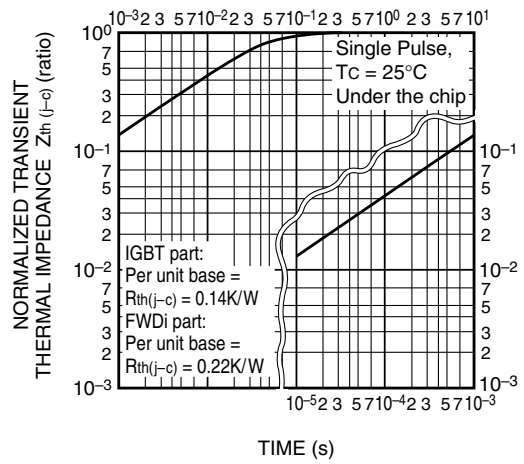
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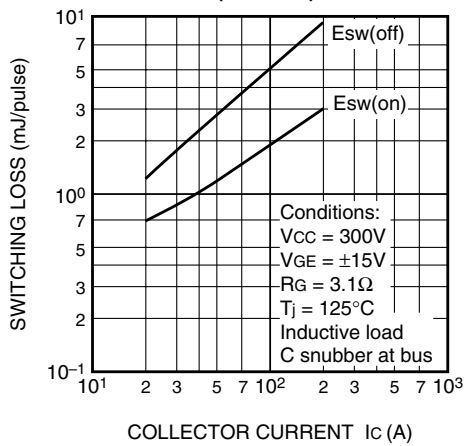
**REVERSE RECOVERY CHARACTERISTICS
OF FREE-WHEEL DIODE
(TYPICAL)**



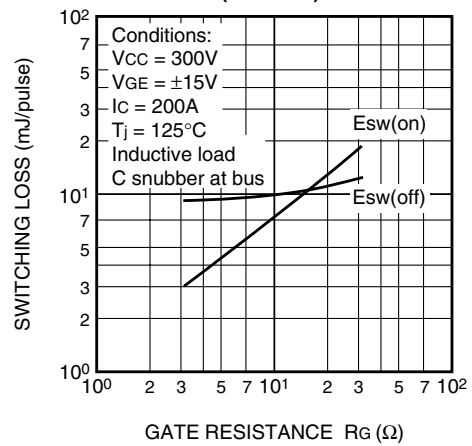
**TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(IGBT part & FWDi part)**



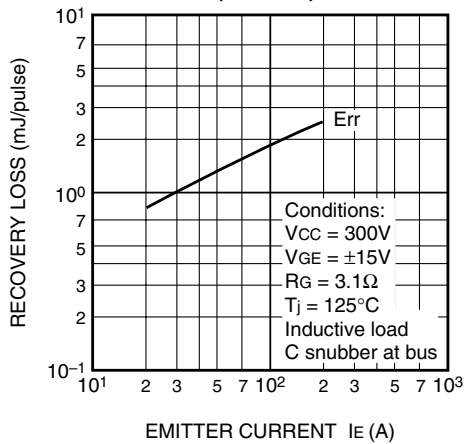
**SWITCHING LOSS vs.
COLLECTOR CURRENT
(TYPICAL)**



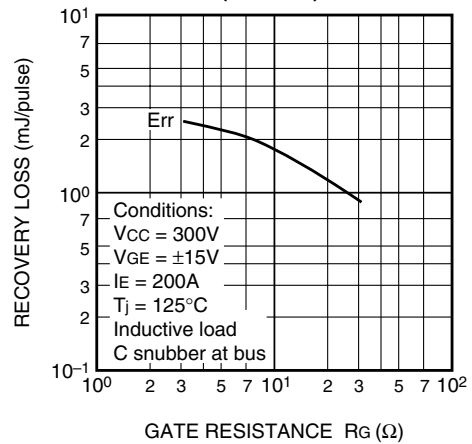
**SWITCHING LOSS vs.
GATE RESISTANCE
(TYPICAL)**



**RECOVERY LOSS vs. IE
(TYPICAL)**



**RECOVERY LOSS vs.
GATE RESISTANCE
(TYPICAL)**



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